

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract as follows:

Abstract

~~An object is~~ In order to improve the soft error resistance of ~~the~~ a memory cell of an SRAM without increasing its chip size. ~~In,~~ in deep through-holes formed by perforating a silicon oxide film, there is a silicon nitride film and a silicon oxide film, a capacitor element having a TiN film serving as a lower electrode, a silicon nitride film serving as an insulator and a TiN film as an upper electrode. This capacitor element is connected between a storage node and a supply voltage line, between a storage node and a reference voltage line, or between storage nodes of the memory cell of the SRAM.